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August 2013



FGA15S125P 1250 V, 15 A Shorted-anode IGBT

Features

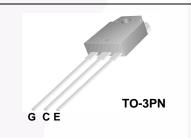
- High Speed Switching
- Low Saturation Voltage: V_{CE(sat)} = 2.25 V @ I_C = 15 A
- High Input Impedance
- RoHS Compliant

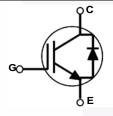
Applications

• Induction Heating, Microwave Oven

General Description

Using advanced field stop trench and shorted-anode technology, Fairchild's shorted-anode trench IGBTs offer superior conduction and switching performances for switching applications. The device can operate in parallel configuration with exceptional avalanche capability . This device is designed for induction heating and microwave oven.





Absolute Maximum Ratings

Symbol	Description		Ratings	Unit
V _{CES}	Collector to Emitter Voltage		1250	V
V _{GES}	Gate to Emitter Voltage		± 25	V
I _C	Collector Current @ $T_{C} = 25^{\circ}C$		30	A
	Collector Current	@ T _C = 100 ^o C	15	A
I _{СМ (1)}	Pulsed Collector Current		45	A
IF	Diode Continuous Forward Current	@ T _C = 25°C	30	A
	Diode Continuous Forward Current	Continuous Forward Current @ $T_{C} = 100^{\circ}C$		A
P _D	Maximum Power Dissipation	@ T _C = 25°C	136	W
	Maximum Power Dissipation	@ T _C = 100 ^o C	68	W
TJ	Operating Junction Temperature		-55 to +175	°C
T _{stg}	Storage Temperature Range		-55 to +175	°C
TL	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds		300	°C

Thermal Characteristics

Symbol	Parameter	Тур.	Max.	Unit
$R_{\theta JC}$ (IGBT)	Thermal Resistance, Junction to Case, Max	-	1.1	°C/W
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction to Ambient, Max	-	40	°C/W

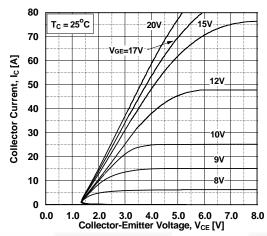
Notes:

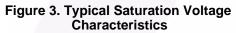
1: Limited by Tjmax

Device	Marking	Device	Package	Reel Size	Таре	Width	Qua	ntity
FGA15	S125P	FGA15S125P	TO-3PN	-		-	;	30
Electric	al Chara	acteristics of	the IGBT T _{c = 2}	25°C unless otherwise noted				
Symbol		Parameter	Test	Conditions	Min.	Тур.	Max.	Unit
Off Chara	cteristics							
ICES	Collector C	Cut-Off Current	V _{CE} = 1250	V, $V_{GE} = 0V$	-	-	1	mA
I _{GES}	G-E Leakage Current		V _{GE} = V _{GES}		-	-	±500	nA
On Chara	cteristics				·			
V _{GE(th)}	1	hold Voltage	I _C = 15mA,		4.5	6.0	7.5	V
GE(01)			-	$I_{C} = 15A, V_{GE} = 15V$				
			$T_{\rm C} = 25^{\rm o}{\rm C}$		-	2.25	2.72	V
V _{CE(sat)}	Collector to	Collector to Emitter Saturation Voltage		_{GE} = 15V	-	2.5	-	V
				_{GE} = 15V,	-	2.75	-	V
			I _F = 15A, T _C = 25°C		-	2	2.55	V
V _{FM}	Diode Forward Voltage		I _F = 15A, T _C	; = 175 ^o C	-	2.55	-	V
Dynamic (Characterist	ics					I	
C _{ies}		ut Capacitance			-	1360	-	pF
C _{oes}	Output Ca	pacitance	$V_{CE} = 30V$	V _{GE} = 0V,	-	40	-	pF
C _{res}	Reverse T	ransfer Capacitance	f = 1 MHZ	f = 1MHz		20	-	pF
Switching	Characteris	tics						
t _{d(on)}	Turn-On D				-	10	-	ns
t _r	Rise Time				_	260	-	ns
t _{d(off)}	Turn-Off D	elay Time	V _{CC} = 600V	/. Ic = 15A.	-	400	-	ns
t _f	Fall Time		R _G = 10Ω, V	V _{GE} = 15V,	-	100	-	ns
E _{on}	Turn-On S	witching Loss	Resistive Lo	oad, T _C = 25ºC	-	0.74	-	mJ
E _{off}	Turn-Off S	witching Loss			-	0.50	-	mJ
E _{ts}	Total Switc	hing Loss			-	1.24	-	mJ
t _{d(on)}	Turn-On D	elay Time			-	11	-	ns
t _r	Rise Time			V _{CC} = 600V, I _C = 15A,		320	-	ns
t _{d(off)}	Turn-Off D	elay Time				420	- /	ns
t _f	Fall Time		$R_G = 10\Omega$, V _{GE} = 15V, Resistive Load,, T _C = 175 ^o C		-	250	- (ns
E _{on}	Turn-On S	witching Loss		Resistive Load,, $\Gamma_{\rm C} = 1/5^{\circ}{\rm C}$		0.94	- \	mJ
E _{off}	Turn-Off S	witching Loss				1.23	-	mJ
E _{ts}	Total Switc	hing Loss			-	2.17	-	mJ
Qg	Total Gate	Charge	\/ 000\	() 45 (-	129	-	nC
Q _{ge}	Gate to En	nitter Charge	V _{CE} = 600V V _{GE} = 15V	, I _C = 15A,	-	9	-	nC
Q _{gc}	Gate to Co	llector Charge			-	66	-	nC

Typical Performance Characteristics







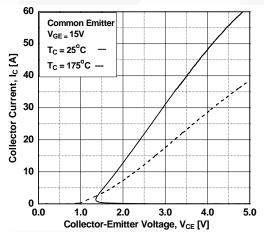


Figure 5. Saturation Voltage vs. Case Temperature at Variant Current Level

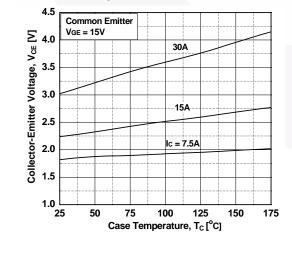


Figure 2. Typical Output Characteristics

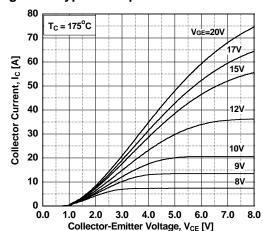


Figure 4. Transfer Characteristics

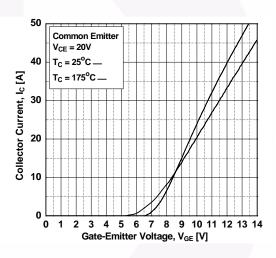
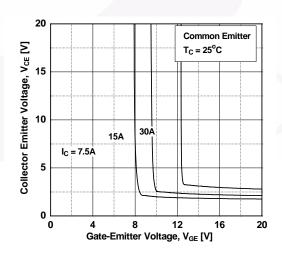
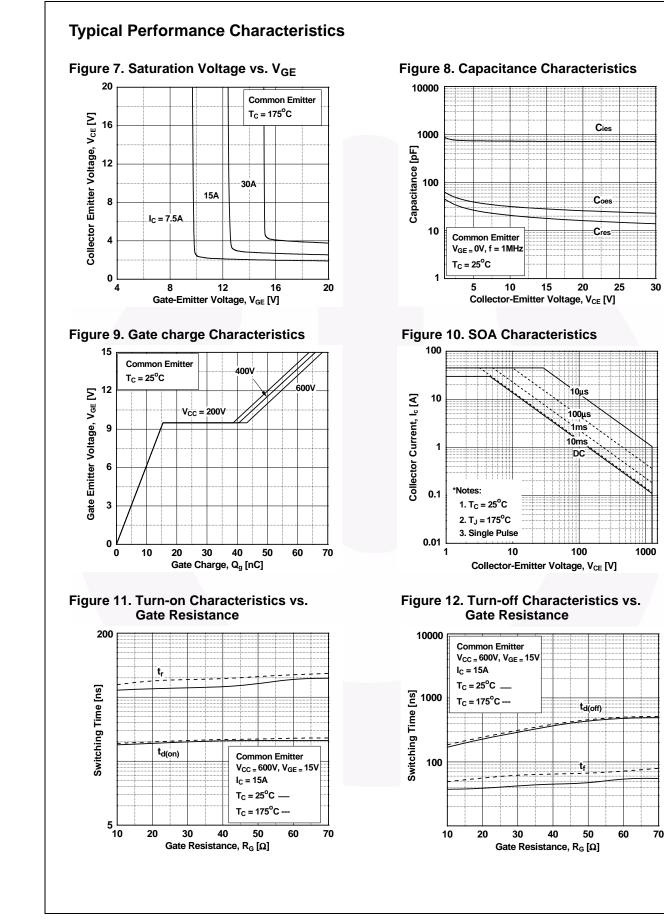


Figure 6. Saturation Voltage vs. V_{GE}

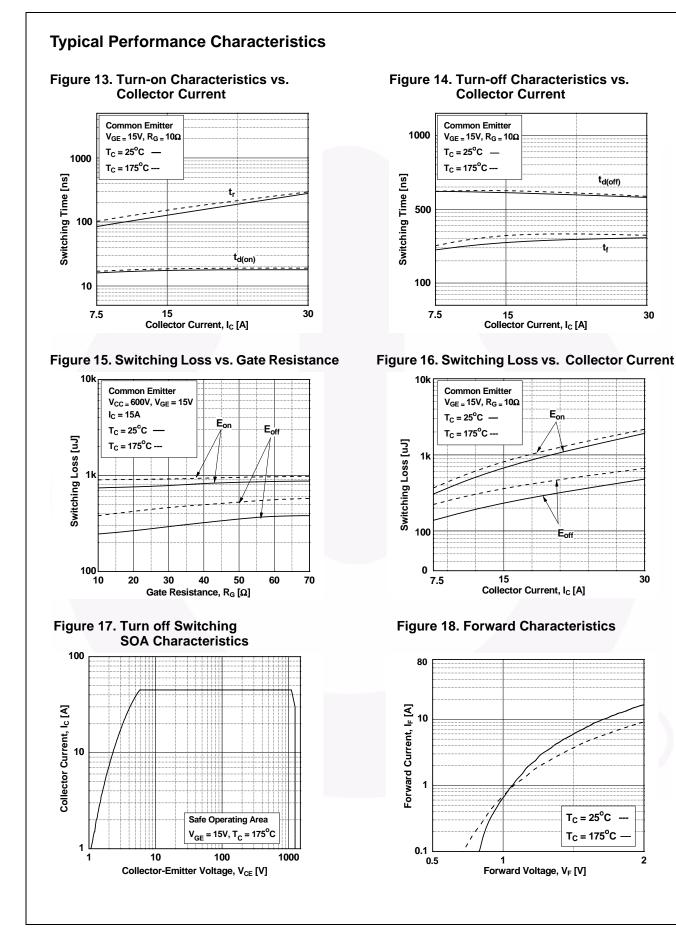


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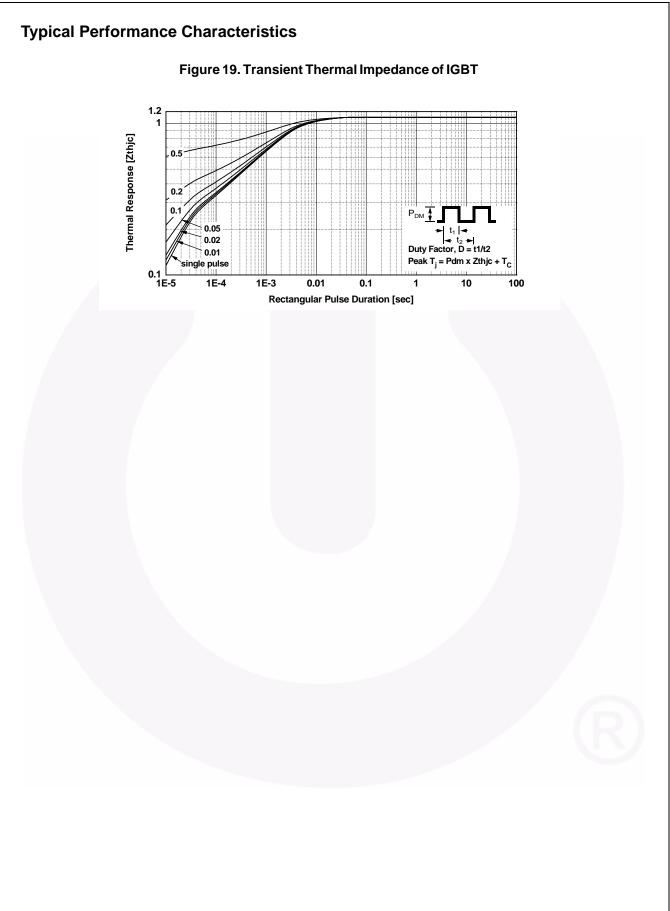
FGA15S125P — 1250 V, 15 A Shorted-anode IGBT

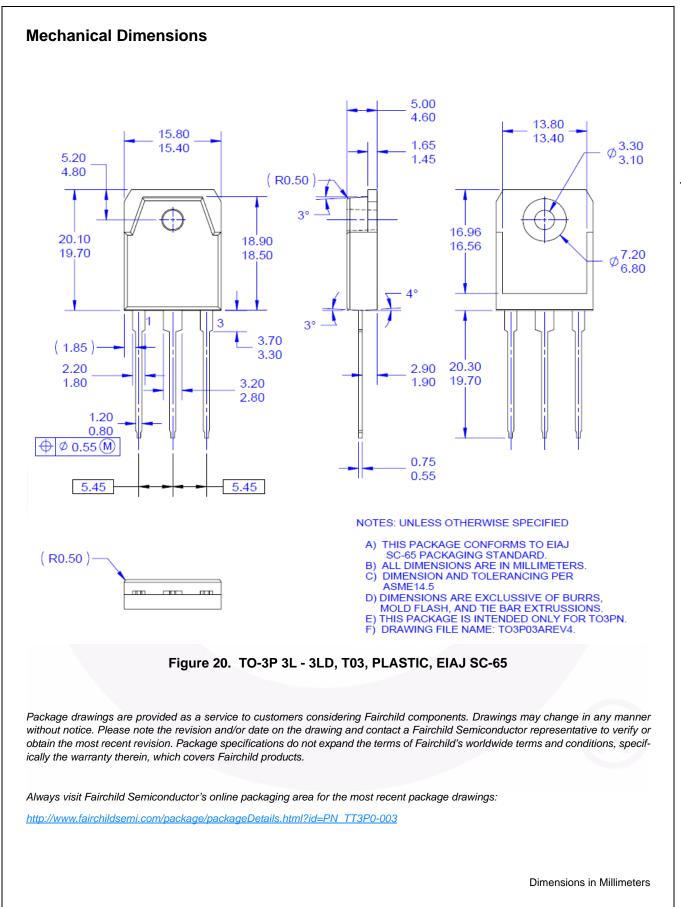


FGA15S125P — 1250 V, 15 A Shorted-anode IGBT



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